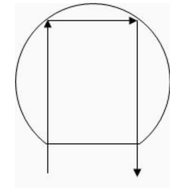
Part Number	Customer

Category		Parameter	Specification	Measurement Method
OverallWafer	1.0	Diameter	100.00 +/- 0.50 mm	WaferVendor
	2.0	Primary Flat Length	32.50 +/- 2.50 mm	Wafer Vendor
	3.0	Primary Flat Orientation	{110}+/-1 degree	Wafer Vendor
	4.0	Overall Thickness	690.00 +/- 10.00 um	ADE, 100%
	5.0	Total Thickness Variation (TTV)	<5.00um	Guaranteed by process
	6.0	Bow	<60.00um	ADE to ASTM F534, 20%
	7.0	Warp	<60.00um	ADE to ASTM F657, 20%
HandleSilicon	8.0	Handle Growth Method	CZ	Wafer Vendor
	9.0	Handle Doping Type	N	Wafer Vendor
	10.0	Handle Dopant	Arsenic	Wafer Vendor
	11.0	Handle Resistivity	<0.005 ohm cm	Wafer Vendor
	12.0	Handle Thickness	690.00 +/- 10.00 um	Wafer Vendor
	13.0	Handle Orientation	<100> +/-0.5	Wafer Vendor
	14.0	Backside Finish	Polished	Wafer Vendor
OverallWafer	15.0	Front Surface Quality	Prime	Wafer Vendor
	16.0	Edge Chips	None	Bright Light 100% (note 2)
	17.0	Edge Rounding	R160/22deg	Wafer Vendor
DeviceSilicon	18.0	Haze	None	Bright Light, 100% (note 2).
	19.0	Scratches	None	Bright Light, 100% (note 2).

Part Number	Customer		
Category	**Parameter**	**Specification**	**Measurement Method**
Shipping Details	Wafer per box :	Max 25	
	Packaging :	Taped Polypropylene Wafer Box Empak, Ultrapak, 100.00mm Antistatic Double Bagging	
	Lot Shipment Data	Device Thickness Bow / Warp Data Handle and SOI Thickness	

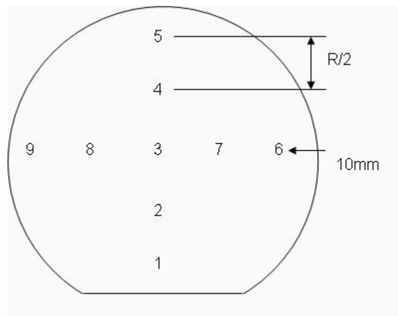
Explanatory Notes

1. Microscope inspection performed using microscope scan as below. 5x objective.



2. All bright light inspections performed exclude all wafer area outside the edge exclusion defined in Overall Wafer, Edge Exclusion. High intensity bright lamp inspection as per ASTM F523.

3. 9 point measurement are as shown in the diagram below:



Additional Information